

2SA673A (PNP) and 2SC1213A (NPN) are silicon epitaxial transistors designed for medium power amplifiers and switching applications. 2SA673A (PNP) is complementary to 2SC1213A (NPN).

T0-92



ECB

ABSOLUTE MAXIMUM RATINGS

| | | |
|--|----------|---------------|
| Collector-Base Voltage | VCBO | 50V |
| Collector-Emitter Voltage | VCEO | 50V |
| Emitter-Base Voltage | VEBO | 4V |
| Collector Current | IC | 500mA |
| Total Power Dissipation | Ptot | 400mW |
| Operating Junction & Storage Temperature | Tj, Tstg | -55 to +150°C |

ELECTRICAL CHARACTERISTICS (TA=25°C)

| PARAMETER | SYMBOL | MIN | MAX | UNIT | TEST CONDITIONS |
|--------------------------------------|----------|----------|-----|------|-------------------|
| Collector Cutoff Current | ICBO | | 500 | nA | VCB=20V IE=0 |
| D.C. Current Gain | HFE | 60 | 320 | | IC=10mA VCE=3V |
| Collector-Emitter Saturation Voltage | VCE(sat) | | 0.4 | V | IC=100mA IB=10mA* |
| Base-Emitter Saturation Voltage | VBE(sat) | | 1 | V | IC=100mA IB=10mA* |
| Collector-Base Breakdown Voltage | BVCBO | 50 | | V | IC=100µA IE=0 |
| Collector-Emitter Breakdown Voltage | LVCEO | 50 | | V | IC=10mA IB=0 |
| Emitter-Base Breakdown Voltage | BVEBO | 4 | | V | IE=100µA IC=0 |
| Current Gain-Bandwidth Product | fT | 120 TYP. | | MHz | IC=10mA VCE=10V |
| Output Capacitance | Cob | 7TYP. | | pF | VCB=10V f=1MHz |



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